



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



企业QQ二维码

## Features

- $BV_{CE0} > 20V$
- $I_C = 2.5A$  Continuous Collector Current
- $R_{CE(sat)} = 50m\Omega$  for a low equivalent On-Resistance
- 625mW Power dissipation
- $h_{FE}$  characterized up to 6A for high current gain hold up
- Complementary NPN type: NK-FMMT718Q

## Mechanical Data

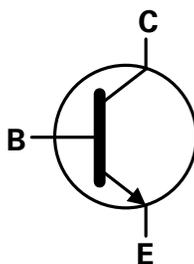
- Package: SOT23
- Package Material: molded plastic, "Green" molding compound  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per  
MIL-STD-202, Method 208 
- Weight 0.008 grams (Approximate)

## Applications

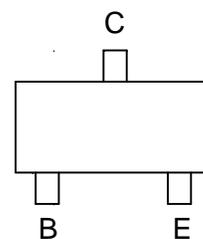
- DC-DC Modules
- Gate Driver
- LED Driver



Top View



Device Symbol



Top View  
Pin-Out

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

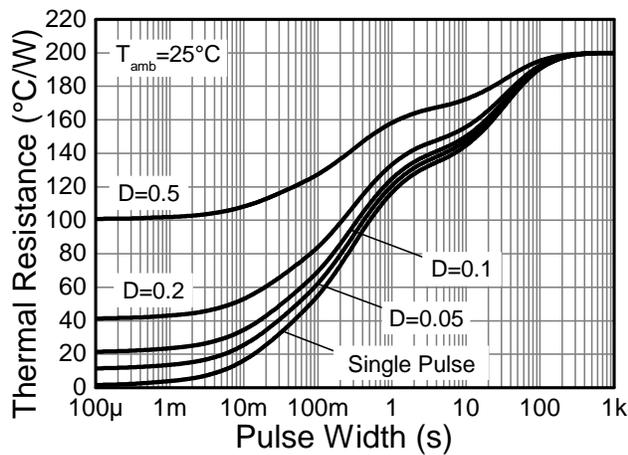
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	2.5	A
Peak Pulse Current	I <sub>CM</sub>	6	A
Base Current	I <sub>B</sub>	500	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

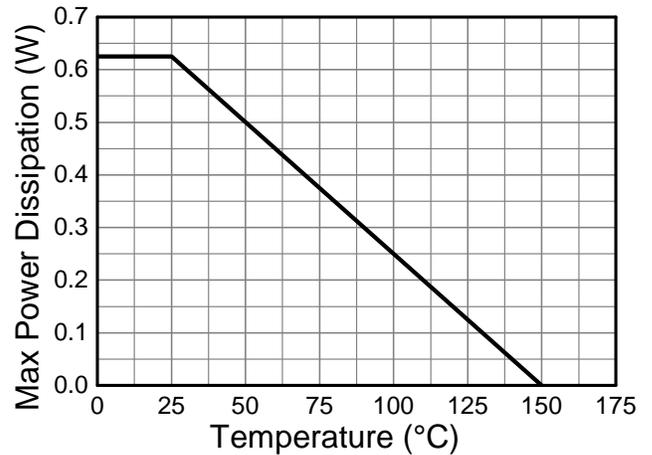
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	625	mW
Power Dissipation (Note 6)	P <sub>D</sub>	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>θJL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  6. Same as note 6, except the device is measured at t ≤ 5 sec.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).

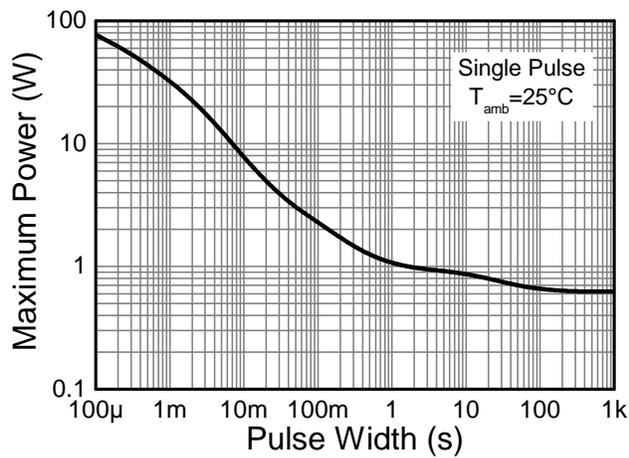
**Thermal Characteristics and Derating information**



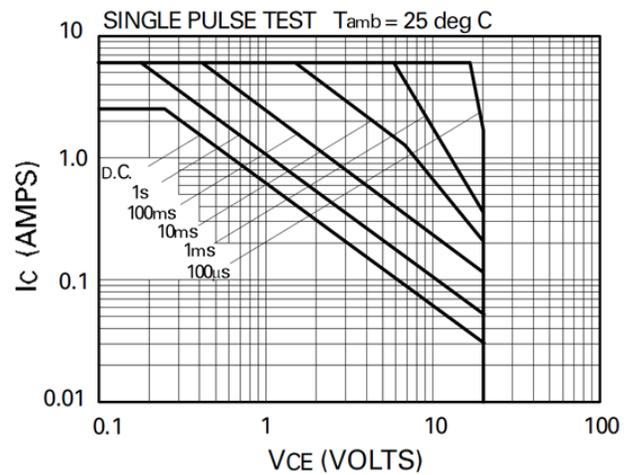
**Fig. 1 Transient Thermal Impedance**



**Fig. 2 Derating Curve**



**Fig. 3 Pulse Power Dissipation**



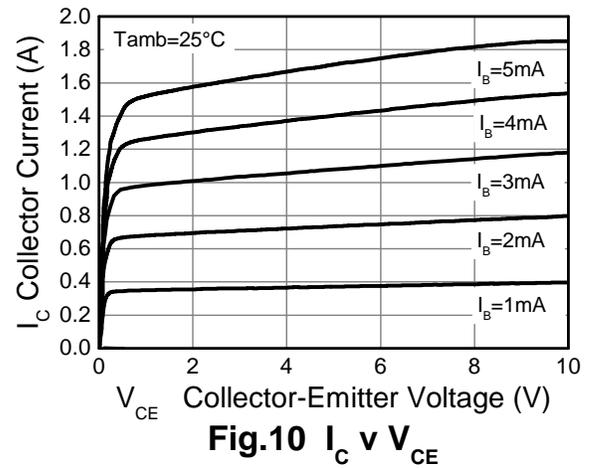
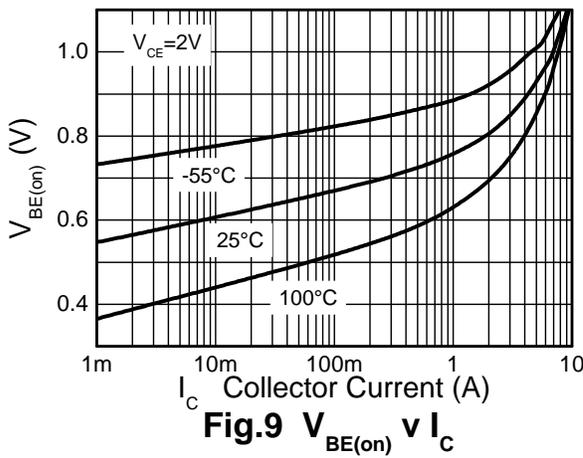
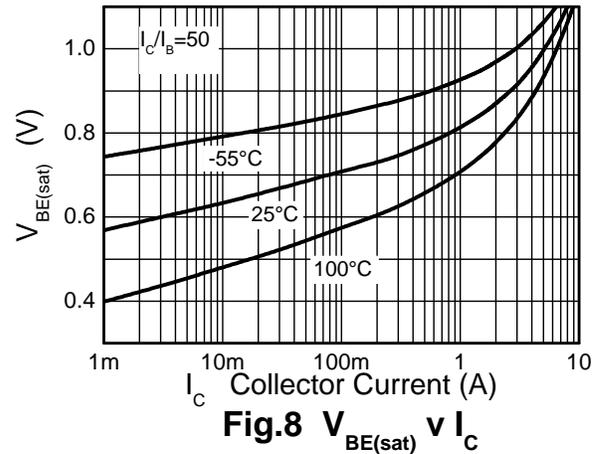
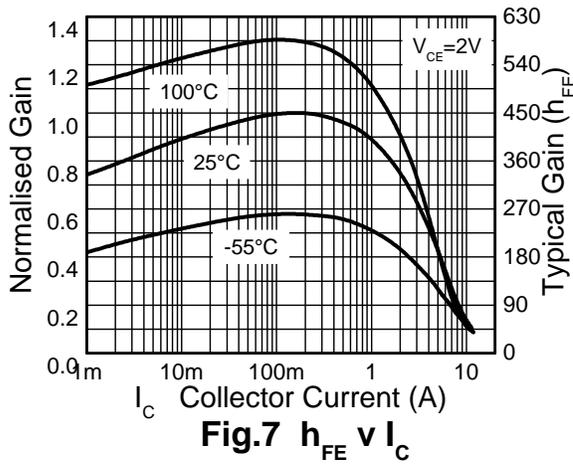
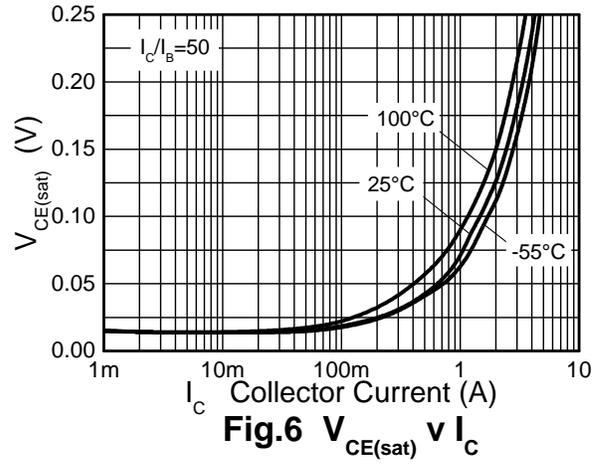
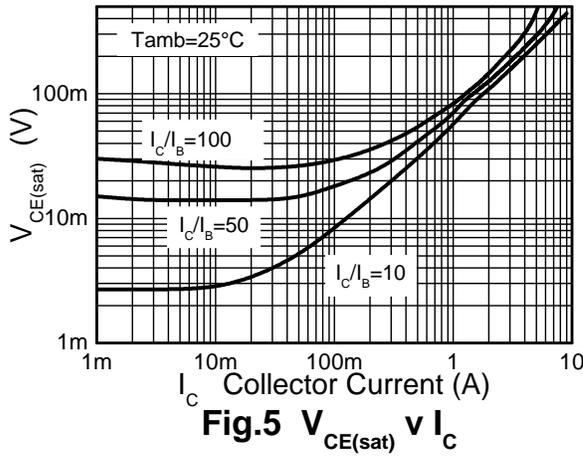
**Fig. 4 Safe Operating Area**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	20	100	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	20	27	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	-	V	I <sub>E</sub> = 100μA
Collector Cut-off Current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> = 20V
Emitter Cut-off Current	I <sub>EBO</sub>	-	-	100	nA	V <sub>EB</sub> = 4V
Collector Emitter Cut-off Current	I <sub>CES</sub>	-	-	100	nA	V <sub>CES</sub> = 20V
Static Forward Current Transfer Ratio (Note 8)	h <sub>FE</sub>	200 300 200 100	400 450 340 150	- - - -	-	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V I <sub>C</sub> = 200mA, V <sub>CE</sub> = 2V I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V I <sub>C</sub> = 6A, V <sub>CE</sub> = 2V
Collector-Emitter Saturation Voltage (Note 8)	V <sub>CE(sat)</sub>	- - -	8 70 130	15 150 200	mV	I <sub>C</sub> = 0.1A, I <sub>B</sub> = 10mA I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA I <sub>C</sub> = 2.5A, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE(sat)</sub>	-	0.89	1	V	I <sub>C</sub> = 2.5A, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE(on)</sub>	-	0.83	1	V	I <sub>C</sub> = 2.5A, V <sub>CE</sub> = 2V
Transition Frequency	f <sub>T</sub>	100	140	-	MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V, f = 100MHz
Collector Output Capacitance	C <sub>obo</sub>	-	23	30	pF	V <sub>CB</sub> = 10V, f = 1MHz
Turn-On Time	t <sub>on</sub>	-	170	-	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A,
Turn-Off Time	t <sub>off</sub>	-	400	-	ns	I <sub>B1</sub> = -I <sub>B2</sub> = 10mA

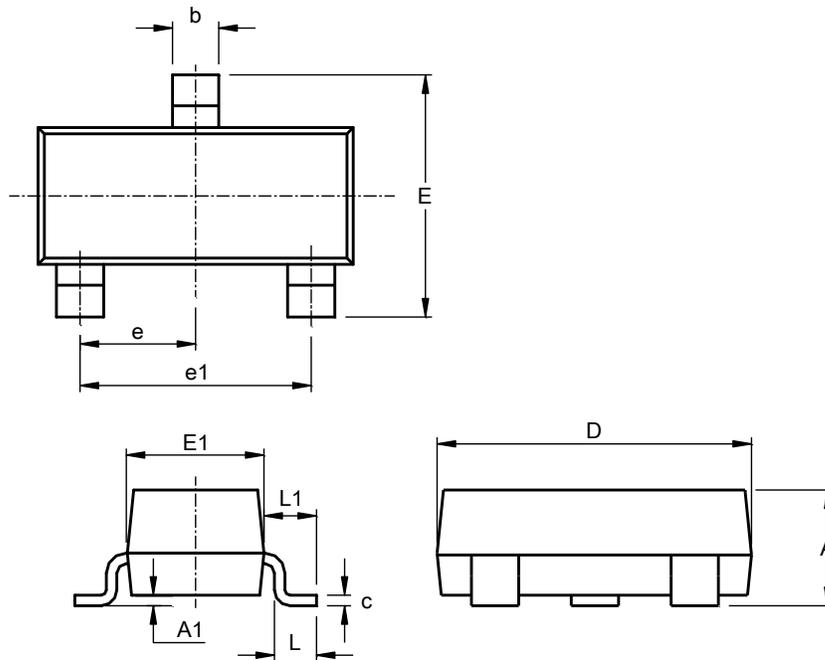
Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)



## Package Outline Dimensions

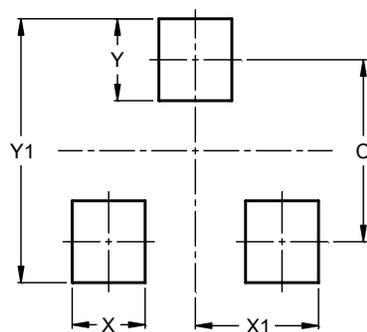
SOT23 (Type DN)



SOT23 (Type DN)			
Dim	Min	Max	Typ
A	0.89	1.12	1.00
A1	0.01	0.10	0.05
b	0.30	0.51	0.45
c	0.08	0.20	0.10
D	2.80	3.04	3.00
E	2.10	2.64	2.42
E1	1.20	1.40	1.37
e	0.95 REF		
e1	1.90 REF		
L	0.25	0.60	0.30
L1	0.45	0.62	0.54
All Dimensions in mm			

## Suggested Pad Layout

SOT23 (Type DN)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9